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C	Substitute for form 1449A/PTO			Complete if Known		
Subs				Application Number	09/296,835	
IN	FORMATIC	N DISC	LOSURE	Filing Date	April 22, 1999	
	STATEMENT BY APPLICANT			First Named Inventor	Ronald A. Weimer	
•	., ., _,,,,			Art Unit	2813	
	(use as many sheets as necessary)			Examiner Name E. Kielin		
Sheet	1	of	1	Attorney Docket Number	M4065.0319/P319	

			'U.S. PA	TENT DOCUMENTS	
Examiner Initials*	Cile No.1	Document Number	Publication Date MM-DD-YYYY		Pages, Columns, Lines, Where Relevant
		Number-Kind Code <sup>2</sup> (If Known)			Passages or Relevant Figures Appôor
EX	Α	6,063,698	05/16/00	Tseng et al.	
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Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ¹ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ¹ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 18 if possible. ⁴ Applicant is to place a check mark here if English language Translation is attached.

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Inilials	Cite No.1	Include name of the author (in CAPITAL LETTERS), tide of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-lasse number(s), publisher, city and/or country where published.	τ²
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EAL	F	LUAN, et al., "Ultra-thin High Quality Ta <sub>2</sub> O <sub>5</sub> Dielectric Prepared by In-Situ Rapid Thermal Processing" Electron Devices Meeting, held 6-9 December 1998, IEDM '98 Technical Digest, pp. 609-612.	

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